

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S78	4	"4116751".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 16:48
S79	104	reus\$6 near10 substrate and (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 17:00
S81	12	(BN or boron near2 nitride) near10 buffer and (gan or gallium near2 nitride) near10 single near2 crystal\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 17:10
S80	35	(BN or boron near2 nitride) same (gan or gallium near2 nitride) near10 single near2 crystal\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 17:10
L2	6	(GaN or gallium adj nitride) near10 lateral and @py<"1997"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 10:55
L1	615	(GaN or gallium adj nitride) near10 lateral	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 10:55
L3	468	(GaN or gallium adj nitride) near10 lateral near4 (grow\$4 or over\$1grow\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 10:56
L6	1810	lateral near4 (grow\$4 or over\$1grow\$5) and @py<"1997"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 10:57
L5	2327	lateral near4 (grow\$4 or over\$1grow\$5) and @py<"2000"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 10:57

L4	13	(GaN or gallium adj nitride) near10 lateral near4 (grow\$4 or over\$1grow\$5) and @py<"2000"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 10:57
L7	41	gallium same lateral near4 (grow\$4 or over\$1grow\$5) and @py<"1997"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 11:00
L9	902	etch\$4 near10 substrate same (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 11:09
L8	11	"iii-v" same lateral near4 (grow\$4 or over\$1grow\$5) and @py<"1997"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 11:09
L10	37	etch\$4 near10 substrate same (gan or gallium near2 nitride) near10 free	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 11:10
L13	293	substrate near15 (gan or gallium near2 nitride) near15 separat\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 11:11
L12	355	substrate same (gan or gallium near2 nitride) near10 separat\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 11:11
L11	53	etch\$4 near10 substrate same (gan or gallium near2 nitride) near10 separat\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 11:11
L14	32	substrate near15 (gan or gallium near2 nitride) near15 separat\$4 and @py<"2000"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 11:19
L15	236	substrate near15 (gan or gallium near2 nitride) near15 (saw\$4 or cleav\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 11:20

L17	1090	reus\$4 near10 substrate and @py<"1999"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 11:35
L16	50	substrate near15 (gan or gallium near2 nitride) near15 (saw\$4 or cleav\$5) and @py<"2000"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 11:35
L18	3	reus\$4 near10 substrate near10 (sapphire or "al.sub.2o.sub.3") and @py<"1999"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 11:37
L19	5	reus\$4 near10 substrate and @py<"1999" and (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 11:53
L20	125	single near5 (gan or gallium near2 nitride) same (gaas or gallium near2 (arsenide or arsenic)) near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 11:56
L21	2	single near5 (gan or gallium near2 nitride) same (alas or algaas or aluminum near2 arsenide or aluminum near2 arsenic) near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 13:28
L22	293	single near2 crystal\$7 near5 (gallium near2 nitride or gan) same ("al.sub.2o.sub.3" or sapphire) near2 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 13:30
L23	30	single near2 crystal\$7 near5 (gallium near2 nitride or gan) same ("al.sub.2o.sub.3" or sapphire) near2 substrate and @py<"1997"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 13:52
L24	3	single near2 crystal\$7 near5 (gallium near2 nitride or gan) same (gaas or gallium near2 arsenide) near2 substrate and @py<"1997"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 13:58
L26	2	"5679152".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 14:04

L25	56	single near2 crystal\$7 near5 (gallium near2 nitride or gan) same (gaas or gallium near2 arsenide) near2 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 14:04
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